

Masakazu Aono

List of Publications by Year in descending order

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248
papers

17,472
citations

24978

57
h-index

13727

129
g-index

252
all docs

252
docs citations

252
times ranked

14899
citing authors

#	ARTICLE	IF	CITATIONS
1	Quantum Conductance in Memristive Devices: Fundamentals, Developments, and Applications. <i>Advanced Materials</i> , 2022, 34, e2201248.	11.1	31
2	Impact of moisture absorption on the resistive switching characteristics of a polyethylene oxide-based atomic switch. <i>Journal of Materials Chemistry C</i> , 2021, 9, 11198-11206.	2.7	6
3	Significant roles of the polymer matrix in the resistive switching behavior of polymer-based atomic switches. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 445301.	1.3	15
4	Tunable Magnetism of Organometallic Nanoclusters by Graphene Oxide On-Surface Chemistry. <i>Scientific Reports</i> , 2019, 9, 14509.	1.6	6
5	Morphological Change of Molecular Assemblies through On-Surface Chemical Reaction. <i>Journal of Physical Chemistry C</i> , 2019, 123, 29679-29685.	1.5	1
6	Reversible manipulation of lattice defects in single-crystal SnO ₂ microrod by applying mechanical stress and voltage. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	1
7	Nanoarchitectonics for Controlling the Number of Dopant Atoms in Solid Electrolyte Nanodots. <i>Advanced Materials</i> , 2018, 30, 1703261.	11.1	59
8	Oxygen vacancy drift controlled three-terminal ReRAM with a reduction in operating gate bias and gate leakage current. <i>Solid State Ionics</i> , 2018, 328, 30-34.	1.3	3
9	Ionic decision-maker created as novel, solid-state devices. <i>Science Advances</i> , 2018, 4, eaau2057.	4.7	28
10	Thermally stable resistive switching of a polyvinyl alcohol-based atomic switch. <i>Journal of Materials Chemistry C</i> , 2018, 6, 6460-6464.	2.7	26
11	Self-Sensitization and Photo-Polymerization of Diacetylene Molecules Self-Assembled on a Hexagonal-Boron Nitride Nanosheet. <i>Polymers</i> , 2018, 10, 206.	2.0	5
12	Highly Reproducible and Regulated Conductance Quantization in a Polymer-Based Atomic Switch. <i>Advanced Functional Materials</i> , 2017, 27, 1605104.	7.8	66
13	Operating mechanism and resistive switching characteristics of two- and three-terminal atomic switches using a thin metal oxide layer. <i>Journal of Electroceramics</i> , 2017, 39, 143-156.	0.8	24
14	Current progress of solid state ionics on information and communication device technology. , 2017, , .		1
15	Ultrahigh-density data storage into thin films of fullerene molecules. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 1102B4.	0.8	9
16	The Way to Nanoarchitectonics and the Way of Nanoarchitectonics. <i>Advanced Materials</i> , 2016, 28, 989-992.	11.1	242
17	Kinetic factors determining conducting filament formation in solid polymer electrolyte based planar devices. <i>Nanoscale</i> , 2016, 8, 13976-13984.	2.8	42
18	Nanoionic devices enabling a multitude of new features. <i>Nanoscale</i> , 2016, 8, 13873-13879.	2.8	24

#	ARTICLE	IF	CITATIONS
19	Nanoionic devices: Interface nanoarchitectonics for physical property tuning and enhancement. Japanese Journal of Applied Physics, 2016, 55, 1102A4.	0.8	17
20	Multiple-probe scanning probe microscopes for nanoarchitectonic materials science. Japanese Journal of Applied Physics, 2016, 55, 1102A7.	0.8	8
21	Self-assembled diacetylene molecular wire polymerization on an insulating hexagonal boron nitride (0001) surface. Nanotechnology, 2016, 27, 395303.	1.3	16
22	Facile fabrication of silk protein sericin-mediated hierarchical hydroxyapatite-based bio-hybrid architectures: excellent adsorption of toxic heavy metals and hazardous dye from wastewater. RSC Advances, 2016, 6, 86607-86616.	1.7	39
23	Nanoarchitectonics. Japanese Journal of Applied Physics, 2016, 55, 1102A6.	0.8	56
24	Self-assembling diacetylene molecules on atomically flat insulators. Physical Chemistry Chemical Physics, 2016, 18, 31600-31605.	1.3	8
25	Nanoarchitectonic atomic switch networks for unconventional computing. Japanese Journal of Applied Physics, 2016, 55, 1102B2.	0.8	47
26	Identification and roles of nonstoichiometric oxygen in amorphous Ta ₂ O ₅ thin films deposited by electron beam and sputtering processes. Applied Surface Science, 2016, 385, 426-435.	3.1	27
27	Mechanism for Conducting Filament Growth in Self-Assembled Polymer Thin Films for Redox-Based Atomic Switches. Advanced Materials, 2016, 28, 640-648.	11.1	128
28	<i>In Situ</i> Tuning of Magnetization and Magnetoresistance in Fe ₃ O ₄ Thin Film Achieved with All-Solid-State Redox Device. ACS Nano, 2016, 10, 1655-1661.	7.3	80
29	Controlled Fabrication of Silk Protein Sericin Mediated Hierarchical Hybrid Flowers and Their Excellent Adsorption Capability of Heavy Metal Ions of Pb(II), Cd(II) and Hg(II). ACS Applied Materials & Interfaces, 2016, 8, 2380-2392.	4.0	65
30	Commentary: Nanoarchitectonics—Think about NANO again. APL Materials, 2015, 3, 061001.	2.2	35
31	Topographic and Electronic Properties of 3,4,9,10-Perylene Tetra Carboxylic Dianhydride (PTCDA) on Indium Tin Oxide (ITO) Surface. Advanced Materials Research, 2015, 1112, 110-115.	0.3	0
32	Redox Reactions at Cu,Ag/Ta ₂ O ₅ Interfaces and the Effects of Ta ₂ O ₅ Film Density on the Forming Process in Atomic Switch Structures. Advanced Functional Materials, 2015, 25, 6374-6381.	7.8	148
33	Ultra-Low Voltage and Ultra-Low Power Consumption Nonvolatile Operation of a Three-Terminal Atomic Switch. Advanced Materials, 2015, 27, 6029-6033.	11.1	15
34	Infrared Aluminum Metamaterial Perfect Absorbers for Plasmon-Enhanced Infrared Spectroscopy. Advanced Functional Materials, 2015, 25, 6637-6643.	7.8	129
35	Nanoarchitectonics: a new materials horizon for nanotechnology. Materials Horizons, 2015, 2, 406-413.	6.4	270
36	Moiré Nanosphere Lithography. ACS Nano, 2015, 9, 6031-6040.	7.3	91

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37	Morphic atomic switch networks for beyond-Moore computing architectures. , 2015, , .		0
38	Plasmon-mediated photocatalytic activity of wet-chemically prepared ZnO nanowire arrays. Physical Chemistry Chemical Physics, 2015, 17, 7395-7403.	1.3	29
39	Dynamic moderation of an electric field using a SiO ₂ switching layer in TaO _x -based ReRAM. Physica Status Solidi - Rapid Research Letters, 2015, 9, 166-170.	1.2	9
40	In Situ and Nonvolatile Photoluminescence Tuning and Nanodomain Writing Demonstrated by All-Solid-State Devices Based on Graphene Oxide. ACS Nano, 2015, 9, 2102-2110.	7.3	36
41	Tunable morphology from 2D to 3D in the formation of hierarchical architectures from a self-assembling dipeptide: thermal-induced morphological transition to 1D nanostructures. Journal of Materials Science, 2015, 50, 3139-3148.	1.7	7
42	Effect of Ionic Conductivity on Response Speed of SrTiO ₃ -Based All-Solid-State Electric-Double-Layer Transistor. ACS Applied Materials & Interfaces, 2015, 7, 12254-12260.	4.0	37
43	Position detection and observation of a conducting filament hidden under a top electrode in a Ta ₂ O ₅ -based atomic switch. Nanotechnology, 2015, 26, 145702.	1.3	19
44	Effects of temperature and ambient pressure on the resistive switching behaviour of polymer-based atomic switches. Journal of Materials Chemistry C, 2015, 3, 5715-5720.	2.7	38
45	Nanoarchitectonics + future leaders = bright success in materials science and technology. Science and Technology of Advanced Materials, 2015, 16, 010302.	2.8	2
46	Ultrahigh-Gain Single SnO ₂ Microrod Photoconductor on Flexible Substrate with Fast Recovery Speed. Advanced Functional Materials, 2015, 25, 3157-3163.	7.8	84
47	Modulation of superconducting critical temperature in niobium film by using all-solid-state electric-double-layer transistor. Applied Physics Letters, 2015, 107, .	1.5	26
48	Synaptic plasticity and memristive behavior operated by atomic switches. , 2014, , .		3
49	Micro x-ray photoemission and Raman spectroscopic studies on bandgap tuning of graphene oxide achieved by solid state ionics device. Applied Physics Letters, 2014, 105, 183101.	1.5	23
50	Nanojunction between Fullerene and One-Dimensional Conductive Polymer on Solid Surfaces. ACS Nano, 2014, 8, 12259-12264.	7.3	25
51	Graphene: In Situ and Non-Volatile Bandgap Tuning of Multilayer Graphene Oxide in an All-Solid-State Electric Double-Layer Transistor (Adv. Mater. 7/2014). Advanced Materials, 2014, 26, 1143-1143.	11.1	2
52	Volatile and nonvolatile selective operation of a two-terminal gap-type atomic switch. , 2014, , .		0
53	In Situ and Non-Volatile Bandgap Tuning of Multilayer Graphene Oxide in an All-Solid-State Electric Double-Layer Transistor. Advanced Materials, 2014, 26, 1087-1091.	11.1	80
54	Benchtop Fabrication of Memristive Atomic Switch Networks. Journal of Nanoscience and Nanotechnology, 2014, 14, 2792-2798.	0.9	7

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55	Generic Relevance of Counter Charges for Cation-Based Nanoscale Resistive Switching Memories. ACS Nano, 2013, 7, 6396-6402.	7.3	216
56	Morphological Transitions from Dendrites to Nanowires in the Electroless Deposition of Silver. Crystal Growth and Design, 2013, 13, 465-469.	1.4	46
57	Ordered Monomolecular Layers as a Template for the Regular Arrangement of Gold Nanoparticles. Langmuir, 2013, 29, 7334-7343.	1.6	8
58	Double-Side-Coated Nanomechanical Membrane-Type Surface Stress Sensor (MSS) for One-Chip One-Channel Setup. Langmuir, 2013, 29, 7551-7556.	1.6	19
59	A theoretical and experimental study of neuromorphic atomic switch networks for reservoir computing. Nanotechnology, 2013, 24, 384004.	1.3	178
60	Quantized Conductance and Neuromorphic Behavior of a Gapless-Type Ag-Ta ₂ O ₅ Atomic Switch. Materials Research Society Symposia Proceedings, 2013, 1562, 1.	0.1	5
61	Influence of Atmosphere on Photo-Assisted Atomic Switch Operations. Key Engineering Materials, 2013, 596, 116-120.	0.4	1
62	Nonvolatile three-terminal operation based on oxygen vacancy drift in a Pt/Ta ₂ O ₅ /Pt, Pt structure. Applied Physics Letters, 2013, 102, 233508.	1.5	12
63	All-solid-state electric-double-layer transistor based on oxide ion migration in Gd-doped CeO ₂ on SrTiO ₃ single crystal. Applied Physics Letters, 2013, 103, .	1.5	47
64	Interconnects with single conjugated polymers. , 2013, , .		0
65	Synaptic plasticity and memory functions achieved in a WO ₃ -based nanoionics device by using the principle of atomic switch operation. Nanotechnology, 2013, 24, 384003.	1.3	117
66	Two Dimensional Array of Piezoresistive Nanomechanical Membrane-Type Surface Stress Sensor (MSS) with Improved Sensitivity. Sensors, 2012, 12, 15873-15887.	2.1	66
67	Impacts of Temperature and Moisture on the Resistive Switching Characteristics of a Cu-Ta ₂ O ₅ -Based Atomic Switch. Materials Research Society Symposia Proceedings, 2012, 1430, 25.	0.1	1
68	Oxygen migration process in the interfaces during bipolar resistance switching behavior of WO ₃ -based nanoionics devices. Applied Physics Letters, 2012, 100, .	1.5	46
69	Flexible Polymer Atomic Switches using Ink-Jet Printing Technique. Materials Research Society Symposia Proceedings, 2012, 1430, 106.	0.1	1
70	Controlled chain polymerisation and chemical soldering for single-molecule electronics. Nanoscale, 2012, 4, 3013.	2.8	68
71	Multilayer Silicene Nanoribbons. Nano Letters, 2012, 12, 5500-5503.	4.5	151
72	On-Demand Nanodevice with Electrical and Neuromorphic Multifunction Realized by Local Ion Migration. ACS Nano, 2012, 6, 9515-9521.	7.3	186

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73	Strain Sensors: Enhancing the Humidity Sensitivity of Ga ₂ O ₃ /SnO ₂ Core/Shell Microribbon by Applying Mechanical Strain and Its Application as a Flexible Strain Sensor (Small 23/2012). Small, 2012, 8, 3598-3598.	5.2	0
74	Selective Adsorption of Thiol Molecules at Sulfur Vacancies on MoS ₂ (0001), Followed by Vacancy Repair via S ⁻ C Dissociation. Journal of Physical Chemistry C, 2012, 116, 22411-22416.	1.5	133
75	Controlling Semiconducting and Insulating States of SnO ₂ Reversibly by Stress and Voltage. ACS Nano, 2012, 6, 7209-7215.	7.3	16
76	Biomimetics: Controlling the Synaptic Plasticity of a Cu ₂ S Gap-Type Atomic Switch (Adv. Funct. Mater.) Tj ETQq0 0,0rgBT /Oylock 10	7.8	1
77	Enhancing the Humidity Sensitivity of Ga ₂ O ₃ /SnO ₂ Core/Shell Microribbon by Applying Mechanical Strain and Its Application as a Flexible Strain Sensor. Small, 2012, 8, 3599-3604.	5.2	25
78	Conductance quantization and synaptic behavior in a Ta ₂ O ₅ -based atomic switch. Nanotechnology, 2012, 23, 435705.	1.3	157
79	One-step fabrication of Î ² -Ga ₂ O ₃ â€œamorphous-SnO ₂ coreâ€œshell microribbons and their thermally switchable humidity sensing properties. Journal of Materials Chemistry, 2012, 22, 12882.	6.7	32
80	Size Effect on the Structure and Optical Properties in Nanocrystalline SrTiO ₃ . E-Journal of Surface Science and Nanotechnology, 2012, 10, 406-410.	0.1	5
81	Forming nanomaterials as layered functional structures toward materials nanoarchitectonics. NPC Asia Materials, 2012, 4, e17-e17.	3.8	366
82	Atomically controlled electrochemical nucleation at superionic solid electrolyte surfaces. Nature Materials, 2012, 11, 530-535.	13.3	208
83	Controlling the Synaptic Plasticity of a Cu ₂ S Gap-Type Atomic Switch. Advanced Functional Materials, 2012, 22, 3606-3613.	7.8	160
84	Effects of Moisture on the Switching Characteristics of Oxide-Based, Gapless-Type Atomic Switches. Advanced Functional Materials, 2012, 22, 70-77.	7.8	247
85	Atomic Switch: Atom/Ion Movement Controlled Devices for Beyond VonNeumann Computers. Advanced Materials, 2012, 24, 252-267.	11.1	338
86	Emergent Criticality in Complex Turing B-Type Atomic Switch Networks. Advanced Materials, 2012, 24, 286-293.	11.1	182
87	Nanoarchitectonics: Pioneering a New Paradigm for Nanotechnology in Materials Development. Advanced Materials, 2012, 24, 150-151.	11.1	95
88	Development and Application of Multiple-Probe Scanning Probe Microscopes. Advanced Materials, 2012, 24, 1675-1692.	11.1	56
89	Unorganized Machines: Emergent Criticality in Complex Turing B-Type Atomic Switch Networks (Adv.) Tj ETQq1 1,0,784314 rgBT /Oye	11.1	0
90	Sensory and short-term memory formations observed in a Ag ₂ S gap-type atomic switch. Applied Physics Letters, 2011, 99, .	1.5	63

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91	Rate-Determining Factors in the Chain Polymerization of Molecules Initiated by Local Single-Molecule Excitation. ACS Nano, 2011, 5, 2779-2786.	7.3	35
92	Molecular-Scale Size Tuning of Covalently Bound Assembly of C60 Molecules. ACS Nano, 2011, 5, 7830-7837.	7.3	21
93	Chemical Wiring and Soldering toward All-Molecule Electronic Circuitry. Journal of the American Chemical Society, 2011, 133, 8227-8233.	6.6	93
94	Macroscopic Superconducting Current through a Silicon Surface Reconstruction with Indium Adatoms: $\langle \text{Si} \rangle$ 111 \hat{a}^{\sim}		

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109	Nonvolatile Crossbar Switch Using $\text{TiO}_x/\text{TaSiO}_y$ Solid Electrolyte. IEEE Transactions on Electron Devices, 2010, 57, 1987-1995.	1.6	36
110	Molecular Scale Control of Unbound and Bound C_{60} for Topochemical Ultradense Data Storage in an Ultrathin C_{60} Film. Advanced Materials, 2010, 22, 1622-1625.	11.1	61
111	Learning Abilities Achieved by a Single Solid-State Atomic Switch. Advanced Materials, 2010, 22, 1831-1834.	11.1	274
112	Photoassisted Formation of an Atomic Switch. Small, 2010, 6, 1745-1748.	5.2	33
113	ZnO-Based Ultraviolet Photodetectors. Sensors, 2010, 10, 8604-8634.	2.1	576
114	Rate-Limiting Processes Determining the Switching Time in a Ag_2S Atomic Switch. Journal of Physical Chemistry Letters, 2010, 1, 604-608.	2.1	99
115	Structural characterization of amorphous Ta_2O_5 and SiO_2 - Ta_2O_5 used as solid electrolyte for nonvolatile switches. Applied Physics Letters, 2010, 97, .	1.5	16
116	Giant Improvement of the Performance of ZnO Nanowire Photodetectors by Au Nanoparticles. Journal of Physical Chemistry C, 2010, 114, 19835-19839.	1.5	319
117	Nonvolatile triode switch using electrochemical reaction in copper sulfide. Applied Physics Letters, 2010, 96, 252104.	1.5	28
118	Nanoionics Switching Devices: "Atomic Switches". MRS Bulletin, 2009, 34, 929-934.	1.7	55
119	First-Principles Study on Electric and Electronic Properties of P-Introduced Si Monatomic Chains. Journal of Computational and Theoretical Nanoscience, 2009, 6, 2635-2639.	0.4	0
120	Metal Nanowire Formation by Solid-Electrochemical Reaction and Its Device Application. Journal of the Vacuum Society of Japan, 2009, 52, 340-346.	0.3	1
121	Nanoscale elemental identification by synchrotron-radiation-based scanning tunneling microscopy. Surface and Interface Analysis, 2008, 40, 1033-1036.	0.8	12
122	Optically monitored wet-chemical preparation of SEIRA active Au nanostructures. Surface and Interface Analysis, 2008, 40, 1681-1683.	0.8	10
123	Reversibility-Controlled Single Molecular Level Chemical Reaction in a C_{60} Monolayer via Ionization Induced by Scanning Transmission Microscopy. Small, 2008, 4, 538-541.	5.2	35
124	A solid electrolyte nanometer switch. Electrical Engineering in Japan (English Translation of Denki) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 0.2		
125	Inelastic scattering in electron transport from a metal tip through a nanoscale metal cluster into a GaAs substrate. Surface Science, 2008, 602, L45-L48.	0.8	2
126	Diffusivity of Cu Ions in Solid Electrolyte and Its Effect on the Performance of Nanometer-Scale Switch. IEEE Transactions on Electron Devices, 2008, 55, 3283-3287.	1.6	121

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127	Effect of sulfurization conditions on structural and electrical properties of copper sulfide films. Journal of Applied Physics, 2008, 103, .	1.1	50
128	Atomic force microscopy and theoretical investigation of the lifted-up conformation of polydiacetylene on a graphite substrate. Soft Matter, 2008, 4, 1041.	1.2	36
129	Structural studies of copper sulfide films: effect of ambient atmosphere. Science and Technology of Advanced Materials, 2008, 9, 035011.	2.8	83
130	The excitation of one-dimensional plasmons in Si and Au@Si complex atom wires. Nanotechnology, 2008, 19, 355204.	1.3	10
131	Nanostencil-Fabricated Electrodes for Electron Transport Measurements of Atomically Thin Nanowires in Ultrahigh Vacuum. Japanese Journal of Applied Physics, 2008, 47, 1797-1799.	0.8	11
132	Low resistivity of Pt silicide nanowires measured using double-scanning-probe tunneling microscope. Applied Physics Letters, 2008, 92, 203114.	1.5	14
133	Editorial Nanosensors for Defense and Security. IEEE Sensors Journal, 2008, 8, 641-646.	2.4	1
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135	Three-Terminal Nanometer Metal Switches Utilizing Solid Electrolytes. IEJ Transactions on Electronics, Information and Systems, 2008, 128, 890-895.	0.1	0
136	Precisely Controlled Fabrication of a Highly Sensitive Au Sensor Film for Surface Enhanced Spectroscopy. Japanese Journal of Applied Physics, 2007, 46, L1222-L1224.	0.8	8
137	Substrate Dependent Low-Temperature Growth of Thin Ag Films: Study on Si(111)@In Surfaces. Japanese Journal of Applied Physics, 2007, 46, 5975-5980.	0.8	6
138	Electronic transport in Ta2O5 resistive switch. Applied Physics Letters, 2007, 91, .	1.5	213
139	In situ Surface-Enhanced Infrared Absorption Spectroscopy for the Analysis of the Adsorption and Desorption Process of Au Nanoparticles on the SiO2/Si Surface. Langmuir, 2007, 23, 6119-6125.	1.6	47
140	Anomalous phase transition and ionic conductivity of AgI nanowire grown using porous alumina template. Journal of Applied Physics, 2007, 102, 124308.	1.1	23
141	Resistance switching of an individual Ag₂S/Ag nanowire heterostructure. Nanotechnology, 2007, 18, 485202.	1.3	89
142	Chain Polymerization of Diacetylene Compound Multilayer Films on the Topmost Surface Initiated by a Scanning Tunneling Microscope Tip. Langmuir, 2007, 23, 5247-5250.	1.6	40
143	Stable molecular orientations of a C60 dimer in a photoinduced dimer row. Carbon, 2007, 45, 1261-1266.	5.4	10
144	Nanoionics-based resistive switching memories. Nature Materials, 2007, 6, 833-840.	13.3	4,518

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145	First-principles study on electronic responses of a C60 molecule to external electric fields. <i>Chemical Physics</i> , 2007, 342, 135-140.	0.9	5
146	Control of local ion transport to create unique functional nanodevices based on ionic conductors. <i>Science and Technology of Advanced Materials</i> , 2007, 8, 536-542.	2.8	31
147	Adsorption and Desorption of Au Nanoparticles Monitored by Infrared Spectroscopy. <i>IEEJ Transactions on Electronics, Information and Systems</i> , 2007, 127, 2171-2174.	0.1	0
148	Effect of sulfurization conditions and post-deposition annealing treatment on structural and electrical properties of silver sulfide films. <i>Journal of Applied Physics</i> , 2006, 99, 103501.	1.1	52
149	Formation of Metastable Silver Nanowires of Hexagonal Structure and Their Structural Transformation under Electron Beam Irradiation. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 6046-6048.	0.8	27
150	Development of a scanning tunneling microscope for in situ experiments with a synchrotron radiation hard-X-ray microbeam. <i>Journal of Synchrotron Radiation</i> , 2006, 13, 216-220.	1.0	45
151	Control of conduction of iodine-doped poly(3-octylthiophene) thin films by double-tip scanning tunneling microscopy. <i>Chemical Physics Letters</i> , 2006, 419, 250-253.	1.2	2
152	Template synthesis of M/M2S (M=Ag, Cu) hetero-nanowires by electrochemical technique. <i>Solid State Ionics</i> , 2006, 177, 2527-2531.	1.3	17
153	Tunneling-current-induced light emission from individual carbon nanotubes. <i>Surface Science</i> , 2006, 600, L15-L19.	0.8	16
154	Fabrication of nanostructures by selective growth of C60 and Si on Si(111) substrate. <i>Surface Science</i> , 2006, 600, 2810-2816.	0.8	13
155	Scanning Tunneling Microscopy Combined with Hard X-ray Microbeam of High Brilliance from Synchrotron Radiation Source. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 1913-1916.	0.8	8
156	Scanning Tunneling Microscope Study of a Local Electronic State Surrounding Mn Nanoclusters on Graphite. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L469-L471.	0.8	2
157	Polaron Injection into One-Dimensional Polydiacetylene Nanowire. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 2049-2052.	0.8	13
158	Application of Simple Mechanical Polishing to Fabrication of Nanogap Flat Electrodes. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L145-L147.	0.8	18
159	Effect of Ion Diffusion on Switching Voltage of Solid-Electrolyte Nanometer Switch. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 3666-3668.	0.8	60
160	Switching Property of Atomic Switch Controlled by Solid Electrochemical Reaction. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L364-L366.	0.8	35
161	Tunneling-Current-Induced Light Emission from Copper Phthalocyanine Thin Films. <i>E-Journal of Surface Science and Nanotechnology</i> , 2006, 4, 559-562.	0.1	6
162	Atomic Switch-Nano Device using the Transfer of Atoms(Ions)-. <i>Hyomen Kagaku</i> , 2006, 27, 232-238.	0.0	3

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163	Solid Electrolyte Nanometer Switch. IEEJ Transactions on Electronics, Information and Systems, 2006, 126, 714-719.	0.1	0
164	Significant increase in conductivity of polydiacetylene thin film induced by iodine doping. Surface Science, 2005, 591, L273-L279.	0.8	35
165	Structural Study of Initial Growth of Nickel on Yttria-Stabilized Zirconia by Coaxial Impact-Collision Ion Scattering Spectroscopy. Japanese Journal of Applied Physics, 2005, 44, 2630-2633.	0.8	0
166	Ionic-Electronic Conductor Nanostructures: Template-Confined Growth and Nonlinear Electrical Transport. Small, 2005, 1, 971-975.	5.2	62
167	Structure of Atomically Smoothed LiNbO ₃ (0001) Surface. Japanese Journal of Applied Physics, 2004, 43, 2057-2060.	0.8	18
168	Epitaxial growth of WO _x nanorod array on W(001). Science and Technology of Advanced Materials, 2004, 5, 647-649.	2.8	23
169	The electron transport properties of photo- and electron-beam-irradiated C ₆₀ films. Journal of Physics and Chemistry of Solids, 2004, 65, 343-348.	1.9	34
170	Conductivity Measurement of Polydiacetylene Thin Films by Double-Tip Scanning Tunneling Microscopy. Journal of Physical Chemistry B, 2004, 108, 16353-16356.	1.2	61
171	Creation of conjugated polymer nanowires through controlled chain polymerization. E-Journal of Surface Science and Nanotechnology, 2004, 2, 99-105.	0.1	6
172	Structural and electrical properties of an electron-beam-irradiated C ₆₀ film. Applied Physics Letters, 2003, 82, 595-597.	1.5	115
173	Structural Analysis of Bismuth Nanowire by X-Ray Standing Wave Method. Japanese Journal of Applied Physics, 2003, 42, 2408-2411.	0.8	13
174	Scanning Tunneling Microscopy Observation of Langmuir-Blodgett Diacetylene Compound Films Deposited by Schaefer's Method. Japanese Journal of Applied Physics, 2002, 41, 2187-2188.	0.8	3
175	Sudden Suppression of Electron-Transmission Peaks in Finite-Biased Nanowires. Japanese Journal of Applied Physics, 2002, 41, 7491-7495.	0.8	4
176	Studies on the nucleation, dynamics and structure of the Si(111)-Ag surface using surface second-harmonic generation. Surface Science, 2002, 517, 65-74.	0.8	8
177	Light creation and propagation in the narrow space between a nanoscale Ag cluster and a tungsten tip. Surface Science, 2001, 495, L834-L838.	0.8	1
178	Nanometer SNS junctions and their application to SQUIDs. Physica C: Superconductivity and Its Applications, 2001, 352, 186-190.	0.6	4
179	Nanoscale control of chain polymerization. Nature, 2001, 409, 683-684.	13.7	433
180	Magnetic-Field-Induced Second-Harmonic Generation on Si(111)-7Å ² . Japanese Journal of Applied Physics, 2001, 40, L1119-L1122.	0.8	10

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181	Study of the Si(111) $\sqrt{5} \times \sqrt{5}$ -Cu Surface Structure by X-Ray Diffraction and Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 2001, 40, L695-L697.	0.8	8
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